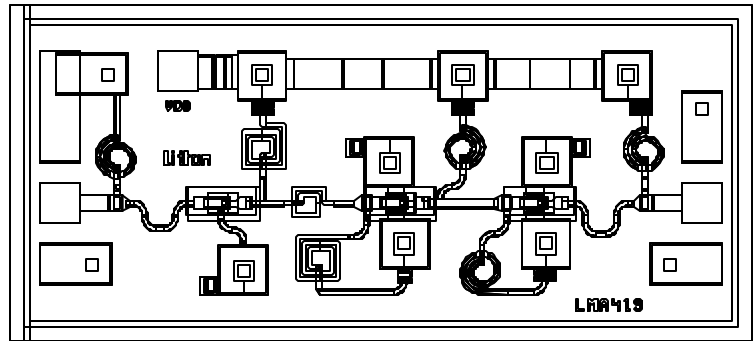


## • FEATURES

- ◆ 18 GHz to 22 GHz Frequency Band
- ◆ 2.5 dB Noise Figure
- ◆ 22 dB Gain
- ◆ 5 dBm Output Power at Saturation
- ◆ 12 dB Input/Output Return Loss
- ◆ +3 V Single Bias Supply



## • DESCRIPTION AND APPLICATIONS

The Filtronic Solid State LMA419 is a low noise PHEMT amplifier that operates from 18 to 22GHz. This 3-stage reactively matched amplifier provides 22dB nominal gain with 2.5dB typical noise figure and saturated power output of +5dBm. The LMA419 is designed for commercial mm-W (millimeter-wave) PCN/PCS applications. Ground is provided to the circuitry through vias to the backside metallization.

## • ELECTRICAL SPECIFICATIONS @ $T_{\text{Ambient}} = 25^{\circ}\text{C}$

( $V_{\text{DD}} = +3.0\text{V}$ ,  $Z_{\text{IN}} = Z_{\text{OUT}} = 50\Omega$ )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Frequency Band	F		18		22	GHz
Small Signal Gain	$S_{21}$	$I_{\text{DS}} = 20 \text{ mA}$	18	22		dB
Small Signal Gain Flatness	$\Delta S_{21}$			$\pm 0.8$	$\pm 1.0$	dB
Noise Figure	NF			2.5	3.0	dB
Input Return Loss	$S_{11}$			-12	-9	dB
Output Return Loss	$S_{22}$			-12	-9	dB
Reverse Isolation	$S_{12}$			-40		dB

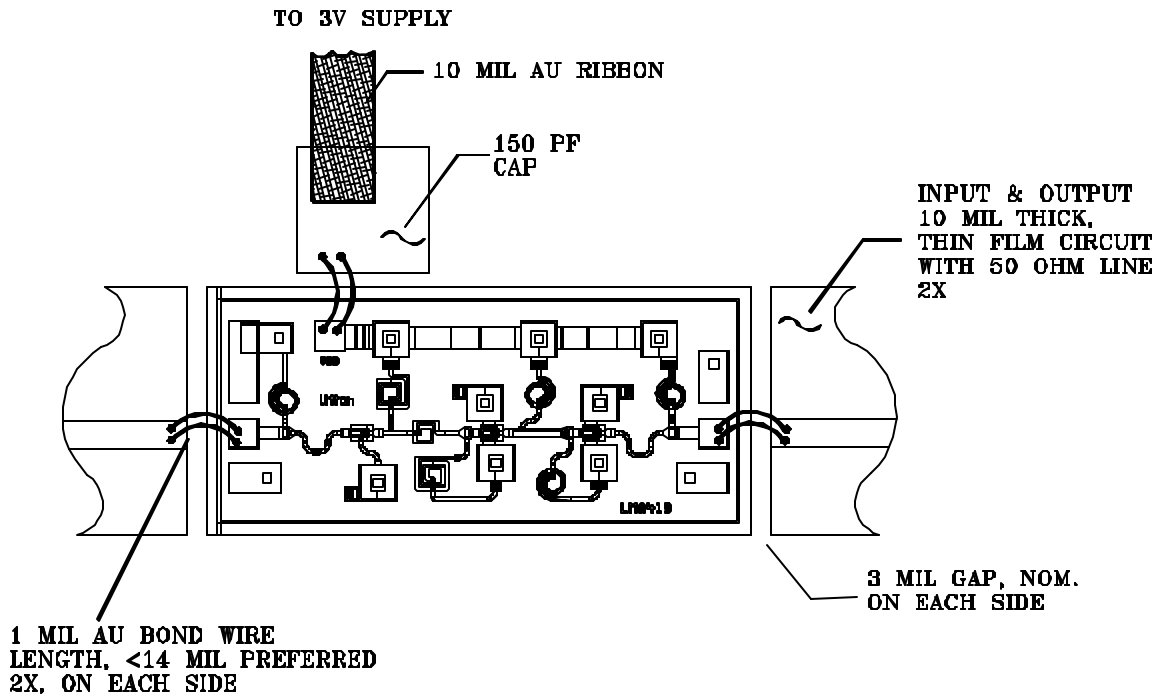
- ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Min	Max	Units
Drain Voltage	$V_D$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		4	V
Operating Current	$I_{OP}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		90	mA
RF Input Power	$P_{IN}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		-10	dBm
Total Power Dissipation	$P_{TOT}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		0.4	W
Channel Operating Temperature	$T_{CH}$	$T_{\text{Ambient}} = 22 \pm 3 \text{ }^\circ\text{C}$		150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	—	-65	165	$^\circ\text{C}$
Maximum Assembly Temperature (1 min. max.)	$T_{MAX}$	—		300	$^\circ\text{C}$

Notes:

- Operating conditions that exceed the Absolute Maximum Ratings could result in permanent damage to the device.
- Recommended Continuous Operating Limits should be observed for reliable device operation.
- Power Dissipation defined as:  $P_{TOT} \equiv (P_{DC} + P_{IN}) - P_{OUT}$ , where  
 $P_{DC}$ : DC Bias Power  
 $P_{IN}$ : RF Input Power  
 $P_{OUT}$ : RF Output Power
- This GaAs MMIC is susceptible to damage from Electrostatic Discharge. Proper precautions should be used when handling these devices.

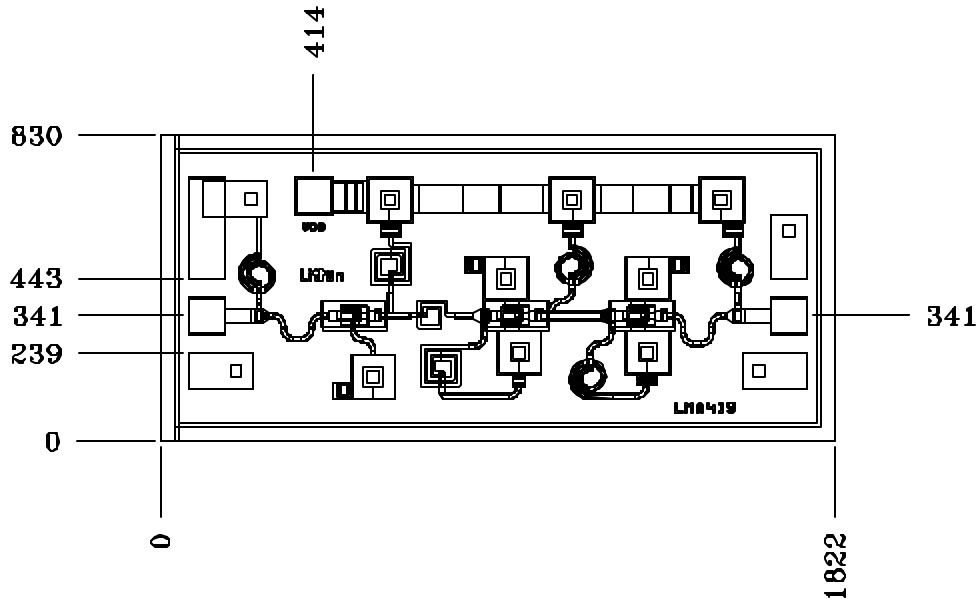
- ASSEMBLY DRAWING



Notes:

- Recommended lead bond technique is thermocompression wedge bonding with 0.001" (25 $\mu$ m) diameter wire. The bond tool force shall be 35-38 gram. Bonding stage temperature shall be 230-240°C, heated tool (150-160°C) is recommended. Ultrasonic bonding is not recommended.
- The recommended die attach is Ablebond silver epoxy, the stabilize bake temperature is set at 150°C for 45 minutes.
- Bond on bond or stitch bond acceptable.
- Conductor over conductor acceptable. Conductors must not short.

- MECHANICAL OUTLINE



Notes:

- All units are in microns ( $\mu\text{m}$ ).
- All bond pads are  $100 \times 100 \mu\text{m}^2$ .
- Bias pad ( $V_{DD}$ ) size is  $100 \times 121.5 \mu\text{m}^2$ .
- Unless otherwise specified.

- HANDLING PRECAUTIONS

To avoid damage to the devices care should be exercised during handling. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. These devices should be treated as Class 1A (0-500 V). Further information on ESD control measures can be found in MIL-STD-1686 and MIL-HDBK-263.

All information and specifications are subject to change without notice.